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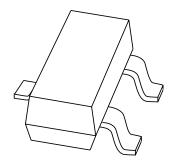
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Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BCW71; BCW72 NPN general purpose transistors

Product data sheet Supersedes data of 1997 Mar 06 1999 Apr 19



## NPN general purpose transistors

**BCW71**; **BCW72** 

#### **FEATURES**

- Low current (100 mA)
- Low voltage (45 V)
- · Low noise.

#### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

NPN transistor in a SOT23 plastic package. PNP complements: BCW69 and BCW70.

#### **MARKING**

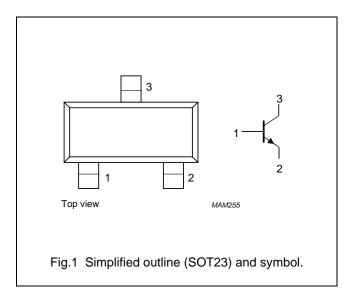
| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BCW71       | K1*                         |
| BCW72       | K2*                         |

#### Note

\* = p : Made in Hong Kong.
 \* = t : Made in Malaysia.

#### **PINNING**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| $V_{CBO}$        | collector-base voltage        | open emitter                     | _    | 50   | V    |
| $V_{CEO}$        | collector-emitter voltage     | open base; I <sub>C</sub> = 2 mA | _    | 45   | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | _    | 5    | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | _    | 100  | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | _    | 200  | mA   |
| I <sub>BM</sub>  | peak base current             |                                  | _    | 200  | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C         | _    | 250  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | -65  | +150 | °C   |
| Tj               | junction temperature          |                                  | _    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | -65  | +150 | °C   |

# NPN general purpose transistors

BCW71; BCW72

#### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                   | CONDITIONS | VALUE | UNIT |  |
|---------------------|---|------------|-------|------|--|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | note 1     | 500   | K/W  |  |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

| SYMBOL             | PARAMETER                       | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|--------------------|---------------------------------|---|------|------|------|------|
| I <sub>CBO</sub>   | collector cut-off current       | I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V                              | _    | _    | 100  | nA   |
|                    |                                 | I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 100 °C     | _    | _    | 10   | μΑ   |
| I <sub>EBO</sub>   | emitter cut-off current         | I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V                               | _    | _    | 100  | μΑ   |
| h <sub>FE</sub>    | DC current gain                 | $I_C = 10 \mu A; V_{CE} = 5 V$  |      |      |      |      |
|                    | BCW71                           |   | _    | 90   | _    |      |
|                    | BCW72                           |   | _    | 150  | _    |      |
|                    | DC current gain                 | I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V                            |      |      |      |      |
|                    | BCW71                           |   | 110  | _    | 220  |      |
|                    | BCW72                           |   | 200  | _    | 450  |      |
| V <sub>CEsat</sub> | collector-emitter saturation    | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$                             | _    | 120  | 250  | mV   |
|                    | voltage                         | I <sub>C</sub> = 50 mA; I <sub>B</sub> = 2.5 mA                         | _    | 210  | _    | mV   |
| V <sub>BEsat</sub> | base-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$                             | _    | 750  | _    | mV   |
|                    |                                 | I <sub>C</sub> = 50 mA; I <sub>B</sub> = 2.5 mA                         | _    | 850  | _    | mV   |
| V <sub>BE</sub>    | base-emitter voltage            | I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V                            | 550  | _    | 700  | mV   |
| C <sub>c</sub>     | collector capacitance           | I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz  | _    | 2.5  | _    | pF   |
| f <sub>T</sub>     | transition frequency            | I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; f = 100 MHz              | 100  | _    | _    | MHz  |
| F                  | noise figure                    | $I_C$ = 200 μA; $V_{CE}$ = 5 V; $R_S$ = 2 kΩ; $f$ = 1 kHz; $B$ = 200 Hz | _    | _    | 10   | dB   |

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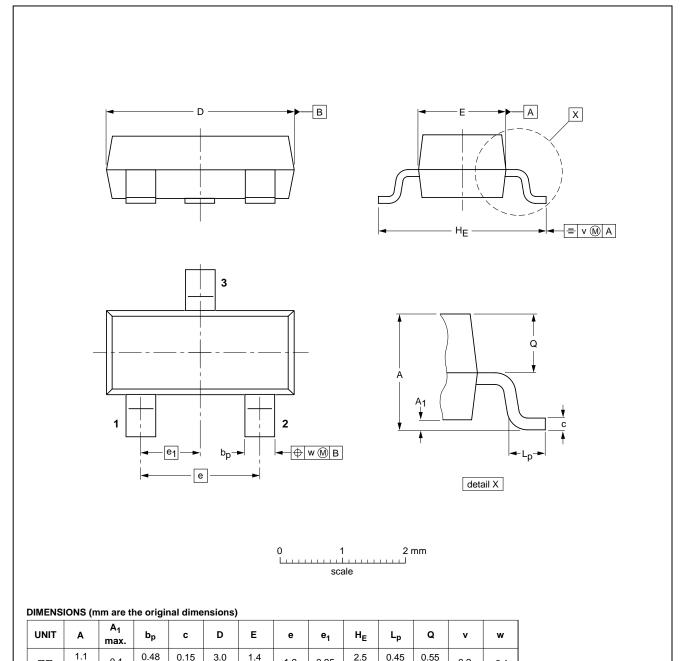
# NPN general purpose transistors

BCW71; BCW72

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



| OUTLINE | REFERENCES |          |      | EUROPEAN | ISSUE DATE |                                  |
|---------|------------|----------|------|----------|------------|----------------------------------|
| VERSION | IEC        | JEDEC    | EIAJ |          | PROJECTION | ISSUE DATE                       |
| SOT23   |            | TO-236AB |      |          |            | <del>-97-02-28</del><br>99-09-13 |

0.1

0.95

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0.1

0.38

### NPN general purpose transistors

**BCW71**; **BCW72** 

#### **DATA SHEET STATUS**

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
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#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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